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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR μ PA1857

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1857 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

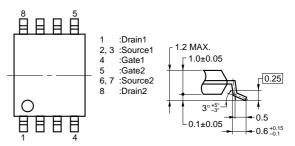
FEATURES

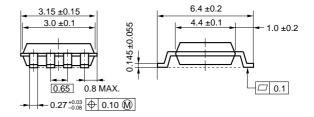
- · Low on-state resistance
 - RDS(on)1 = 67.0 m Ω MAX. (Vgs = 10 V, ID = 2.0 A)
 - $R_{DS(on)2} = 86.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.5 \text{ V, ID} = 2.0 \text{ A)}$
 - $R_{DS(on)3} = 95.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.0 \text{ V, Ip} = 2.0 \text{ A)}$
- Low Ciss Ciss = 580 pF TYP.
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

| PART NUMBER | PACKAGE |
|---------------|--------------|
| μPA1857GR-9JG | Power TSSOP8 |

PACKAGE DRAWING (Unit: mm)

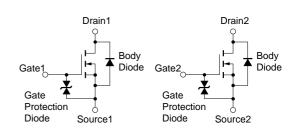




ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

| Drain to Source Voltage (Vgs = 0 V) | VDSS | 60 | V |
|--|--------------------|-------------|----|
| Gate to Source Voltage (Vps = 0 V) | Vgss | ±20 | V |
| Drain Current (DC) (T _A = 25°C) | I _{D(DC)} | ±3.8 | Α |
| Drain Current (pulse) Note1 | ID(pulse) | ±15.2 | Α |
| Total Power Dissipation (1 unit) Note2 | P _{T1} | 1.0 | W |
| Total Power Dissipation (2unit) Note2 | P _{T2} | 1.7 | W |
| Channel Temperature | Tch | 150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |
| Single Avalanche Current Note3 | las | 3.8 | Α |
| Single Avalanche Energy Note3 | Eas | 33 | mJ |
| | | | |

EQUIVALENT CIRCUIT



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - **2.** TA = 25° C Mounted on ceramic substrate of 50 cm² x 1.1 mm
 - 3. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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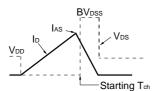
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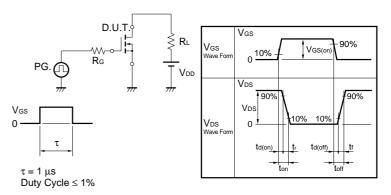
ELECTRICAL CHARACTERISTICS (TA = 25°C)

| CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|--|------|------|------|------|
| Zero Gate Voltage Drain Current | loss | Vps = 60 V, Vgs = 0 V | | | 10 | μΑ |
| Gate Leakage Current | Igss | Vgs = ±20 V, Vps = 0 V | | | ±10 | μΑ |
| Gate Cut-off Voltage | V _{GS(off)} | V _{DS} = 10 V, I _D = 1 mA | 1.5 | 2.0 | 2.5 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} = 10 V, I _D = 2.0 A | 2.5 | 5.4 | | S |
| Drain to Source On-state Resistance | RDS(on)1 | Vgs = 10 V, ID = 2.0 A | | 53 | 67.0 | mΩ |
| | RDS(on)2 | Vgs = 4.5 V, ID = 2.0 A | | 64 | 86.0 | mΩ |
| | RDS(on)3 | Vgs = 4.0 V, ID = 2.0 A | | 71 | 95.0 | mΩ |
| Input Capacitance | Ciss | Vps = 10 V | | 580 | | pF |
| Output Capacitance | Coss | V _G s = 0 V | | 100 | | pF |
| Reverse Transfer Capacitance | Crss | f = 1 MHz | | 50 | | pF |
| Turn-on Delay Time | td(on) | VDD = 30 V, ID = 2.0 A | | 10 | | ns |
| Rise Time | tr | Vgs = 10 V | | 9 | | ns |
| Turn-off Delay Time | t d(off) | $R_G = 6 \Omega$ | | 32 | | ns |
| Fall Time | tf | | | 4 | | ns |
| Total Gate Charge | Q _G | V _{DD} = 48 V | | 12 | | nC |
| Gate to Source Charge | Qgs | V _G S = 10 V | | 2 | | nC |
| Gate to Drain Charge | Q _{GD} | ID = 3.8 A | | 3 | | nC |
| Body Diode Forward Voltage | V _F (S-D) | IF = 3.8 A, VGS = 0 V | | 0.80 | | V |
| Reverse Recovery Time | trr | IF = 3.8 A, VGS = 0 V | | 33 | | ns |
| Reverse Recovery Charge | Qrr | di/dt = 100 A / μs | | 58 | | nC |

TEST CIRCUIT 1 AVALANCHE CAPABILITY



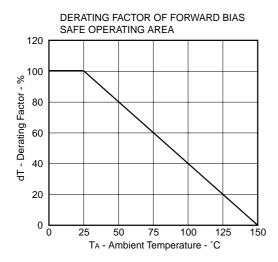
TEST CIRCUIT 2 SWITCHING TIME

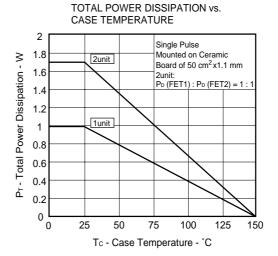


TEST CIRCUIT 3 GATE CHARGE

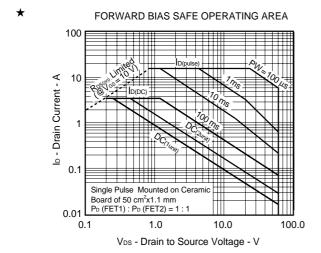


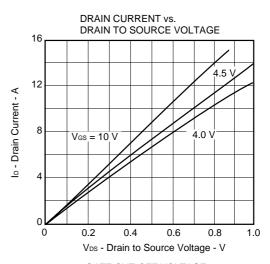
TYPICAL CHARACTERISTICS (TA = 25°C)

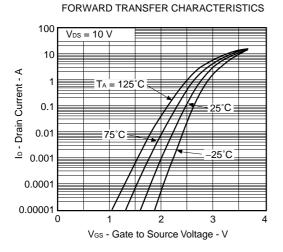


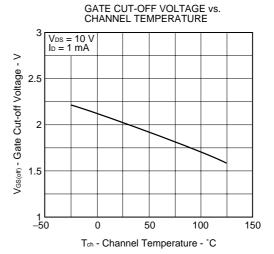


uPA1857

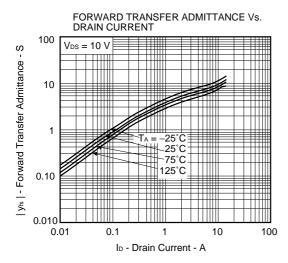




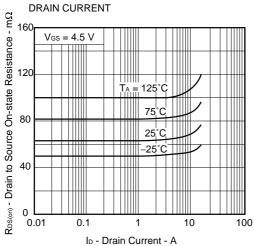




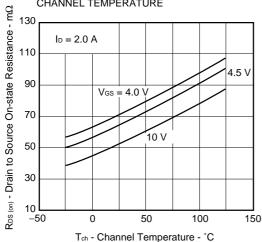
3



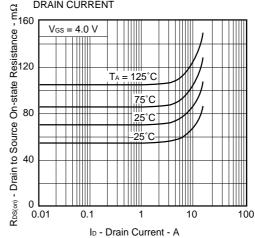
DRAIN TO SOURCE ON-STATE RESISTANCE vs.



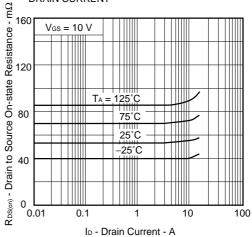
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



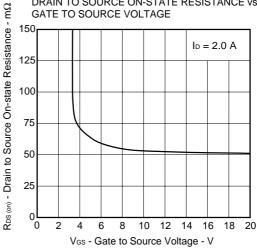
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

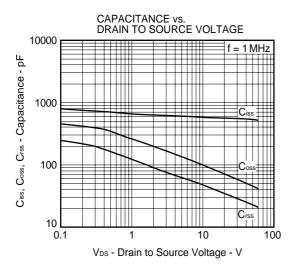


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

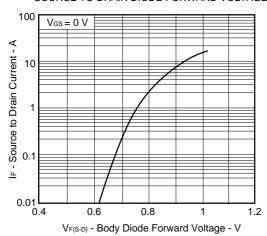


DRAIN TO SOURCE ON-STATE RESISTANCE vs.

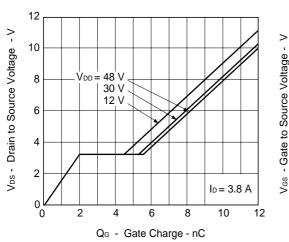




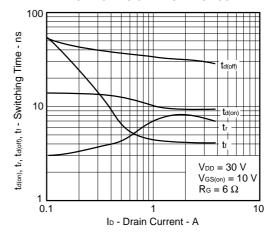
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



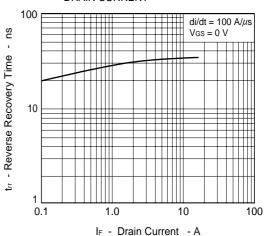
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



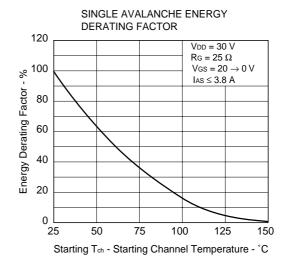
SWITCHING CHARACTERISTICS



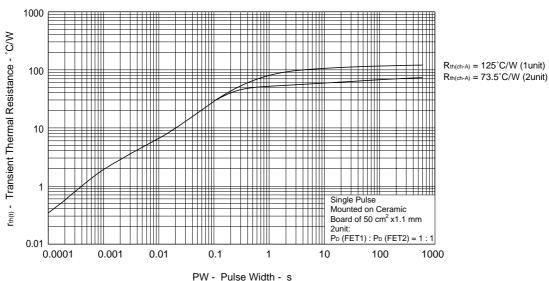
REVERSE RECOVERY TIME vs. DRAIN CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD 10 V-tuelload Inductive Load Inductive Load Vode = 30 V RG = 25 Ω VGs = 20 \rightarrow 0 V Starting T_{ch} = 25°C 10 μ 100 μ 1m 10m L - Inductive Load - H



★ TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



[MEMO]

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